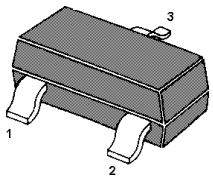
PBSS5240T

Plastic-Encapsulate Transistors (PNP)



SOT-23

1. BASE
2. EMITTER
3. COLLECTOR

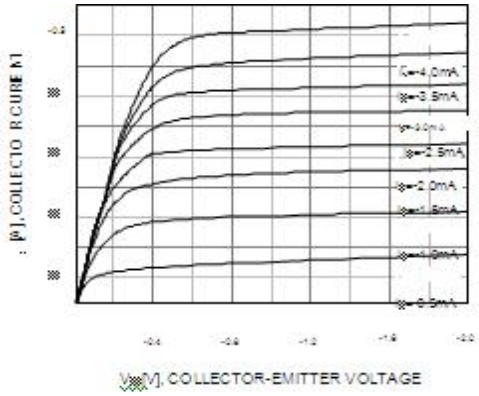
MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

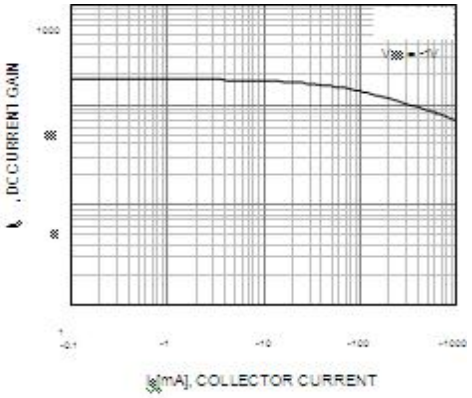
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

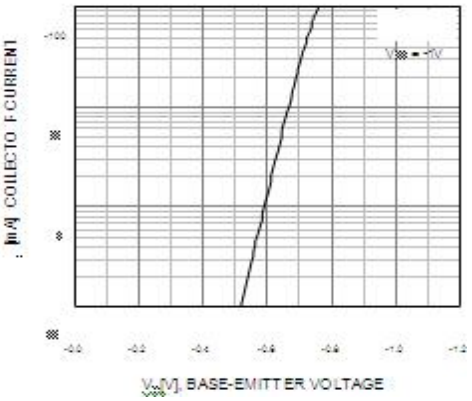
ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

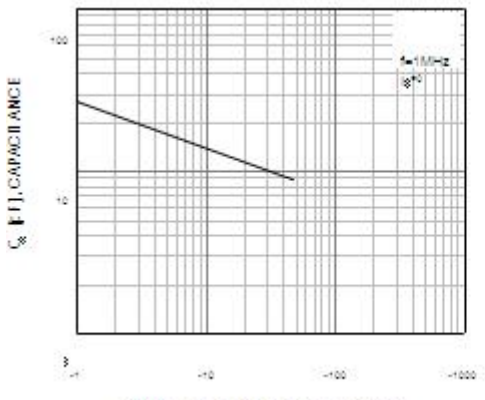
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA, I_E=0	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-0.1mA, I_B=0	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}=-40V, I_E=0		-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-20V, I_B=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V, I_C=-100mA	200	350	
	$h_{FE(2)}$	V_{CE}=-1V, I_C=-800mA	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-800mA, I_B=-80mA		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-800mA, I_B=-80mA		-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	I_C=-1V, V_{CE}=-10mA		-1	V
Base-emitter positive favor voltage	V_{BEF}	I_B=-1A		-1.55	V
Transition frequency	f_T	V_{CE}= -10V, I_C= -50mA f=30MHz	100		MHz
output capacitance	C_{ob}	(V_{CB}=-10V,I_E=0,f=1MHz)		20	pF

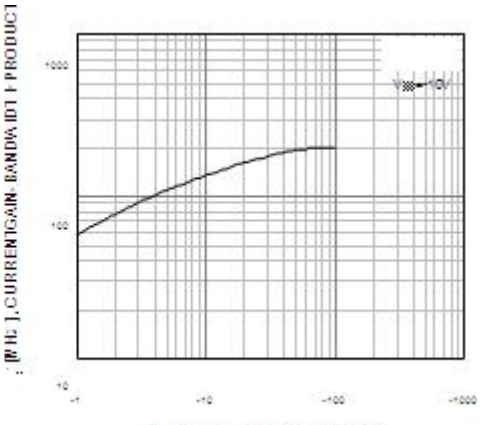
Typical Characteristics



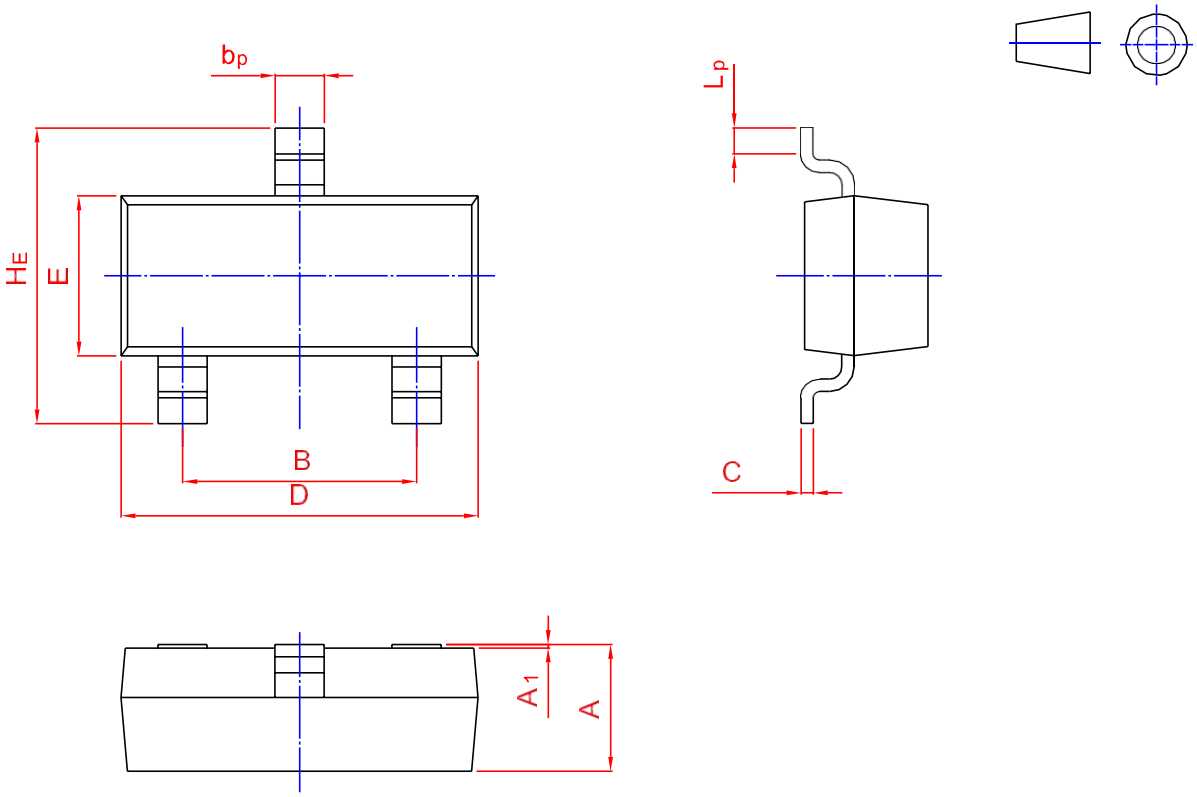








Plastic surface mounted package; 3 leads **SOT-23**



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20